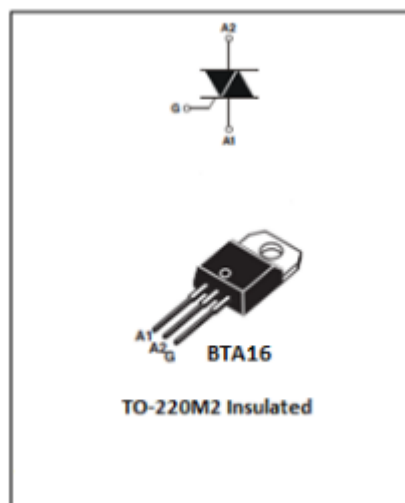


DESCRIPTION:

The BTA/B16 triac series is suitable to fit all models of control Found in applications such as motor control ,industrial and domestic lighting ,heating and static switching , motor speed controllers,...

By using an internal ceramic pad, the BTA series provides voltage insulated tab (rated at2500VRMS) complying with UL standards



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM} V_{RRM}	600/800/1000	V
V_{TM}	1.55	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	Tstg	-40 ~150	°C
Operating junction temperature range	Tj	-40~125	°C
Repetitive peak off-state voltage (T =25°C)	V_{DRM}	600/800/1000	V
Repetitive peak reverse voltage (T =25°C)	V_{RRM}	600/800/1000	V
RMS on-state current	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	160	A
I ² t value for fusing (tp=10ms)	I ² t	144	A ² S
Critical rate of rise of on-state current (I =2×I _{GT})	dI/dt	50	A/μS
Peak gate current	I_{GM}	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W

ELECTRICAL CHARACTERISTICS (T=25°C unless otherwise specified)
3 Quadrants

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I_{GT}	$V = 12V$ $R = 33\Omega$	I II III	MAX.	5	10	35	50	mA
V_{GT}		I II III	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$ $T_j = 125^\circ C$ $R = 3.3K\Omega$	I II III	MIN.	0.2				V
I_L	$I_G = 1.2I_{GT}$	III III	MAX.	15	30	80	100	mA
I_H	$I_T = 100mA$		MAX.	10	15	40	50	mA
dV/dt	$V_D = 2/3V_{DRM}$ Gate Open $T_j = 125^\circ C$		MIN.	20	40	800	1000	V/ μs

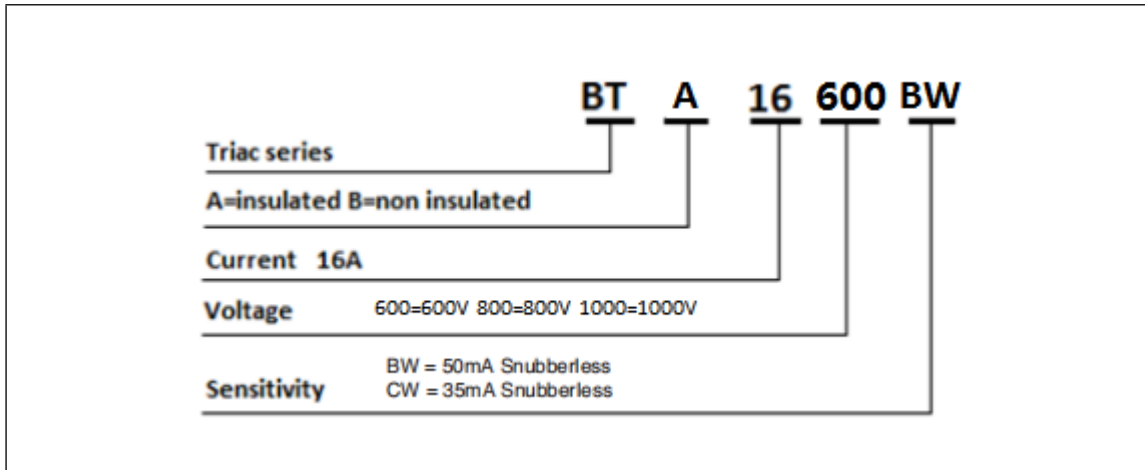
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM} = 22.5A$ $t_p = 380\mu s$	$T_j = 25^\circ C$	1.55	V
I_{DRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_j = 25^\circ C$	5	μA
I_{RRM}		$T_j = 125^\circ C$	1	mA

Thermal Resistances

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	junction to ambient	60	$^\circ C/W$
$R_{th(j-c)}$	Junction to case(AC)	2.1	

Ordering Information Scheme



TO-220M2 Package Mechanical Data

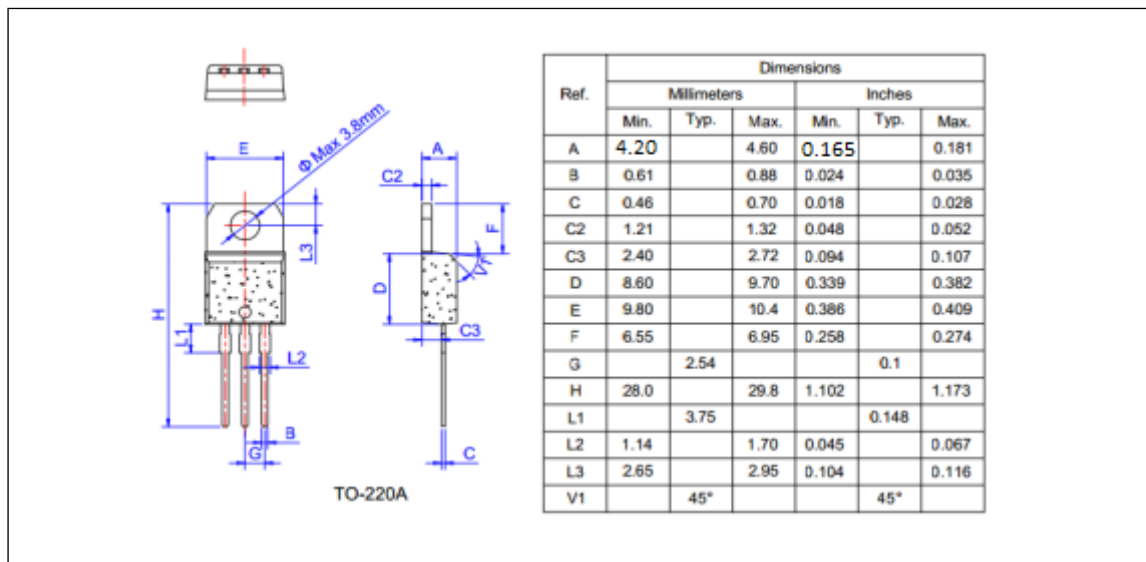


FIG.1 Maximum power dissipation versus RMS on-state current

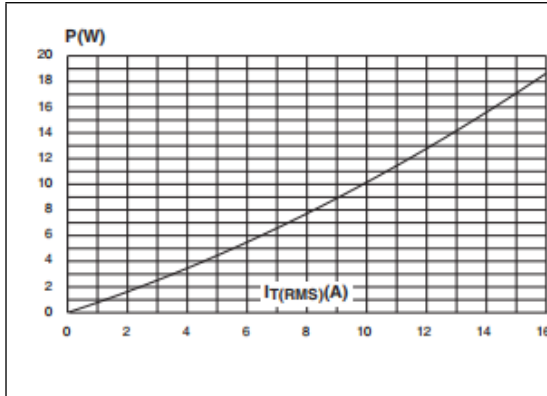


FIG.2: RMS on-state current versus case temperature

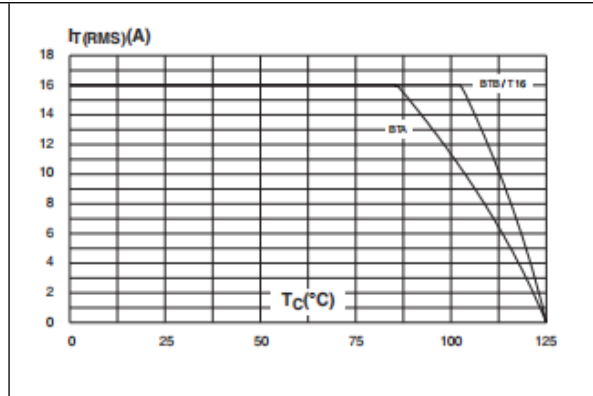


FIG.3: Surge peak on-state current versus number of cycles

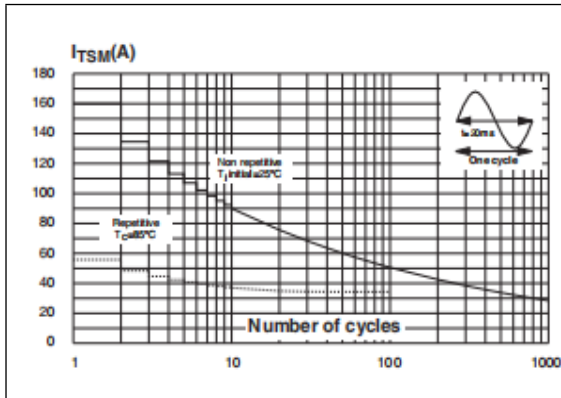


FIG.4: On-state characteristics (maximum values)

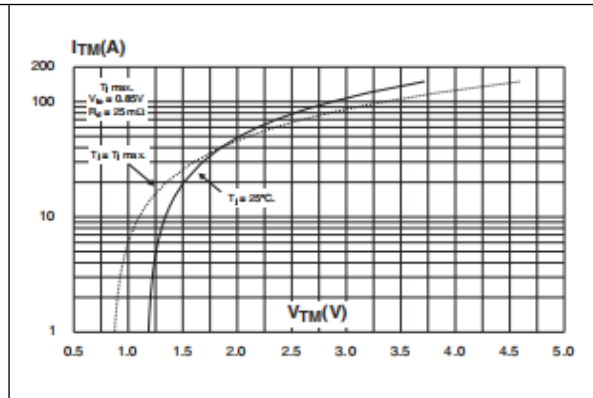


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of $I^2 t$ ($di/dt < 50\text{A}/\mu\text{s}$)

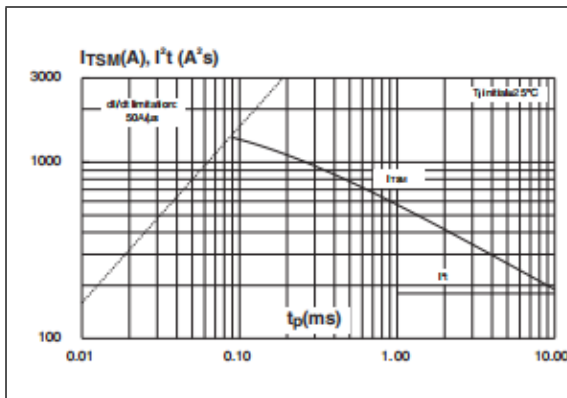


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature

